

| L Number | Hits | Search Text | DB | Time stamp |
|---------------------|-------------|---|--|-----------------------------|
| 201 | 97 | ((first or second) near (tft or (thin near film near transistor))) and ((first or second) near (gate near (oxide or insulator or dielectric or insulation))) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/25 20:23 |
| 202 | 45 | ((first or second) near (tft or (thin near film near transistor))) and ((first or second) near (gate near (oxide or insulator or dielectric or insulation))) and ((first or second) near (gate adj electrode)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/25 20:24 |
| 203 | 32 | ((first or second) near (tft or (thin near film near transistor))) and ((first or second) near (gate near (oxide or insulator or dielectric or insulation))) and ((first or second) near (gate adj electrode)) and ((low or high or lightly or highly) near3 (dope or doped or doping or impurity or density) or (ldd or hdd)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/25 20:36 |
| 204 | 3 | ((first or second) near (tft or (thin near film near transistor))) and ((first or second) near (gate near (oxide or insulator or dielectric or insulation))) and ((first or second) near (gate adj electrode)) and ((low or high or lightly or highly) near3 (dope or doped or doping or impurity or density) or (ldd or hdd)) and (matsumoto or lee or wakai or seo or yamaguchi) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/25 20:30 |
| 205 | 13 | ((first or second) near (tft or (thin near film near transistor))) and ((first or second) near (gate near (oxide or insulator or dielectric or insulation))) and ((first or second) near (gate adj electrode)) and ((low or high or lightly or highly) near3 (dope or doped or doping or impurity or density) or (ldd or hdd)) and (semiconductor adj layer) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/25 20:47 |
| 206 | 6 | ((first or second) near (tft or (thin near film near transistor))) and ((first or second) near (gate near (oxide or insulator or dielectric or insulation))) and ((first or second) near (gate adj electrode)) and ((semiconductor near layer) near10 ((low or high or lightly or highly) near3 (dope or doped or doping or impurity or density) or (ldd or hdd))) and (semiconductor adj layer) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/25 20:40 |